

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
60V	4.0Ω @ V _{GS} = 10V	247mA
	4.1Ω @ V _{GS} = 5V	244mA
	5.0Ω @ V _{GS} = 4V	221mA

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

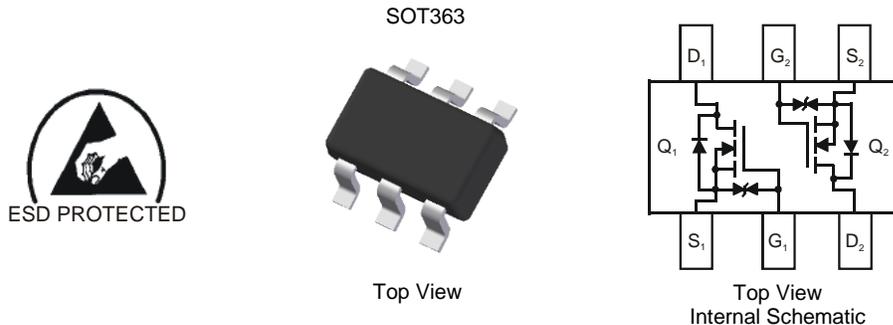
- Motor Control
- Power Management Functions
- Backlighting

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](#) or your local Diodes representative.**
- <https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Alloy42 Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (Approximate)



Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002DWS-7	SOT363	3000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



MM1 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: G = 2019)
 M = Month (ex: 9 = September)

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025	2026	2027		
Code	F	G	H	I	J	K	L	M	N	O		
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	60	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	247	mA
		T _A = +70°C		198	
Maximum Body Diode Forward Current (Note 6)			I _S	247	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	1.8	A
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	1.8	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	0.29	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	438	°C/W
Total Power Dissipation (Note 6)			P _D	0.37	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	341	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	V _{GS} = 0V, I _D = 10µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	µA	V _{DS} = 60V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	—	2.5	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	1.89	4.0	Ω	V _{GS} = 10V, I _D = 0.5A
			1.85	4.1		V _{GS} = 5V, I _D = 0.2A
			1.97	5.0		V _{GS} = 4V, I _D = 0.2A
Diode Forward Voltage	V _{SD}	—	0.8	1.1	V	V _{GS} = 0V, I _S = 115mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	41	—	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	4.4	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	2.6	—	pF	f = 1MHz, V _{GS} = 0V, V _{DS} = 0V
Gate Resistance	R _g	—	900	—	Ω	
Total Gate Charge	Q _g	—	0.4	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 250mA
Gate-Source Charge	Q _{gs}	—	0.2	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.1	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	3.7	—	ns	V _{DD} = 30V, V _{GS} = 10V, R _g = 25Ω, I _D = 200mA
Turn-On Rise Time	t _r	—	3.6	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	102	—	ns	
Turn-Off Fall Time	t _f	—	22	—	ns	
Reverse Recovery Time	t _{RR}	—	20	—	ns	I _F = 1A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	—	7.9	—	nC	I _F = 1A, di/dt = 100A/µs

- Notes:
- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 - Device mounted on 1" × 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

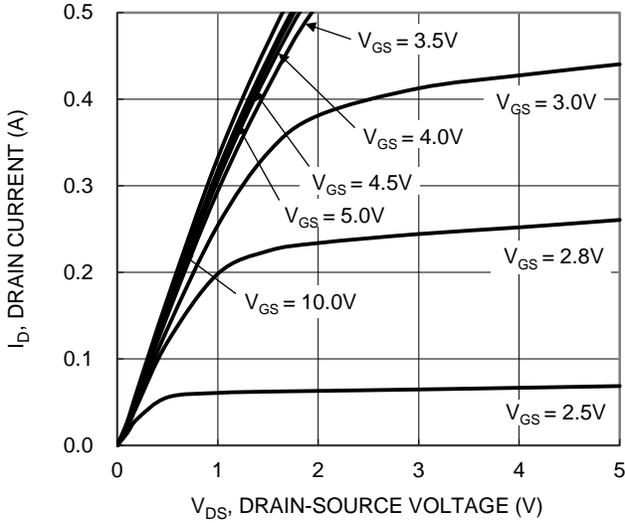


Figure 1. Typical Output Characteristic

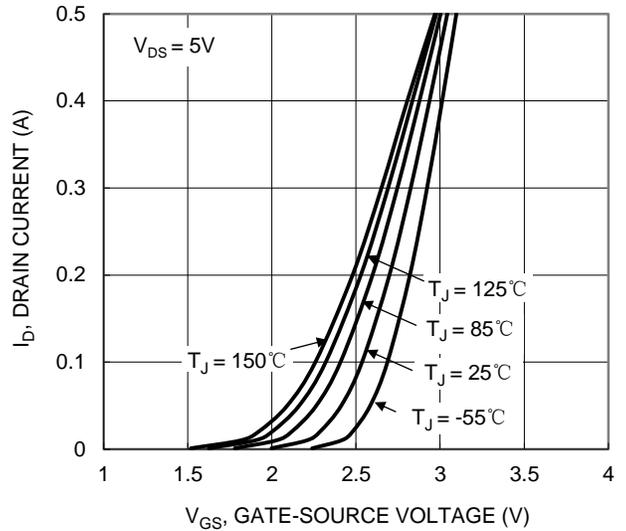


Figure 2. Typical Transfer Characteristic

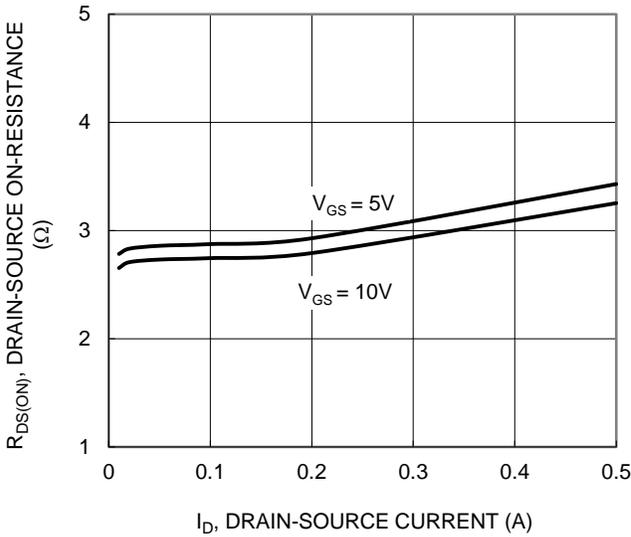


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

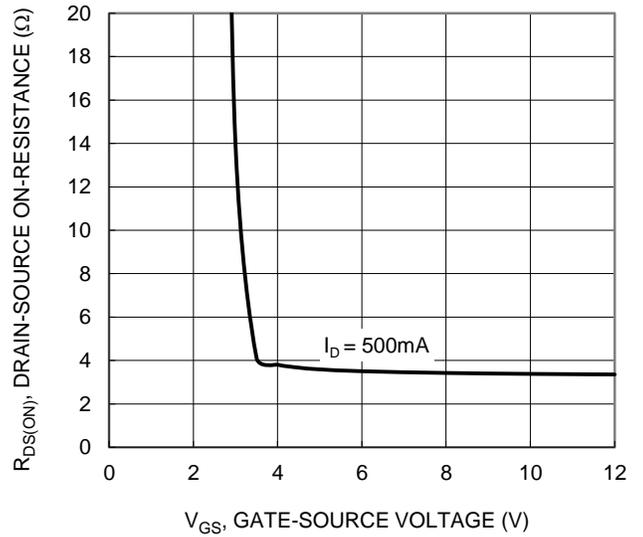


Figure 4. Typical Transfer Characteristic

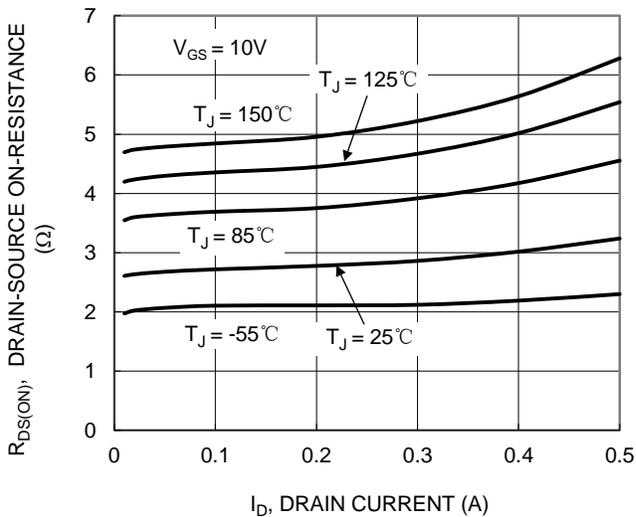


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

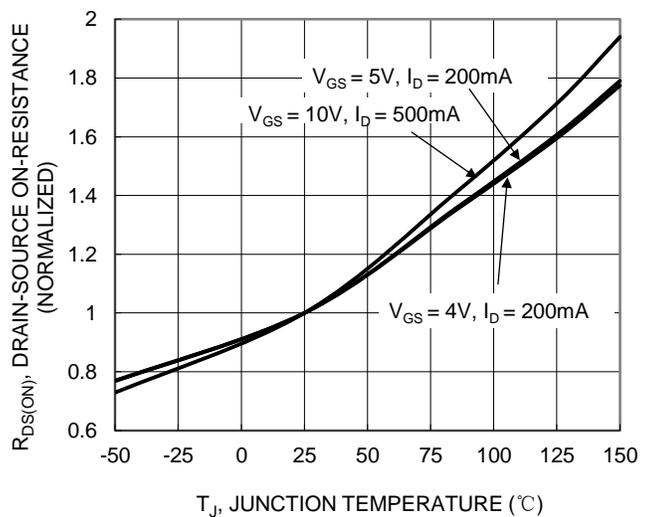


Figure 6. On-Resistance Variation with Junction Temperature

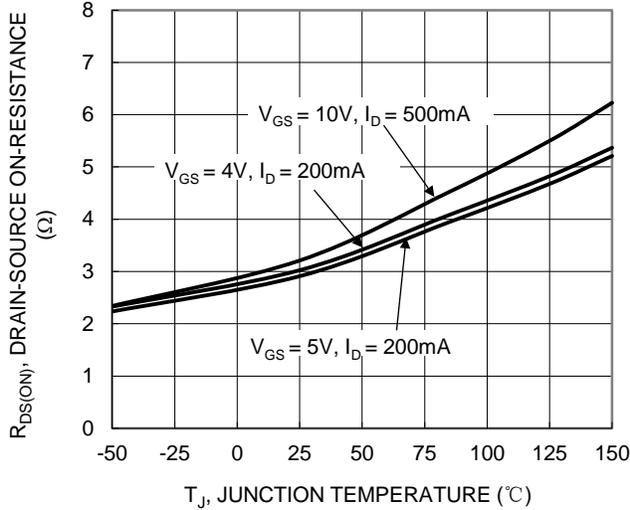


Figure 7. On-Resistance Variation with Junction Temperature

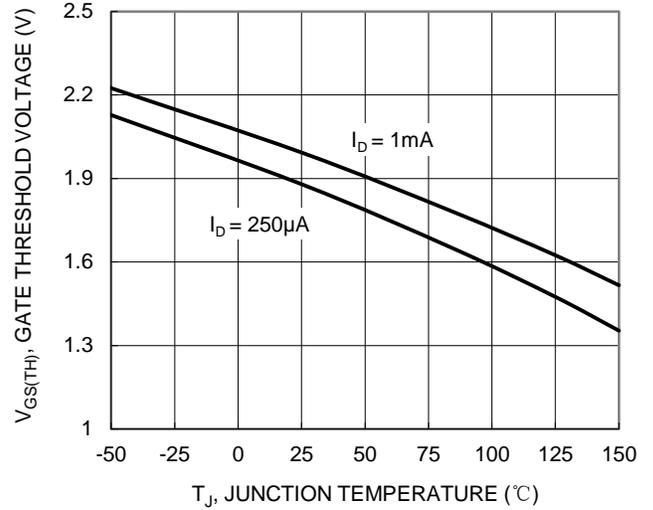


Figure 8. Gate Threshold Variation vs. Junction Temperature

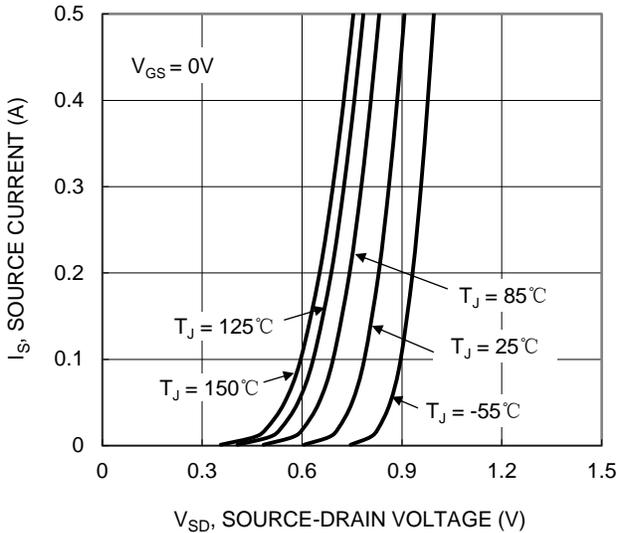


Figure 9. Diode Forward Voltage vs. Current

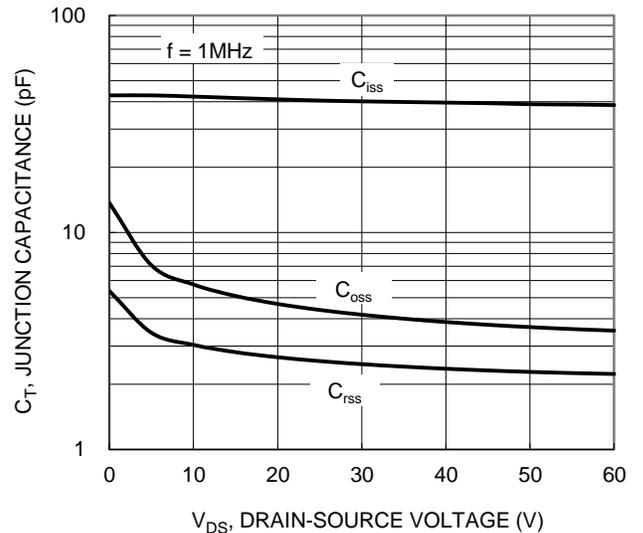


Figure 10. Typical Junction Capacitance

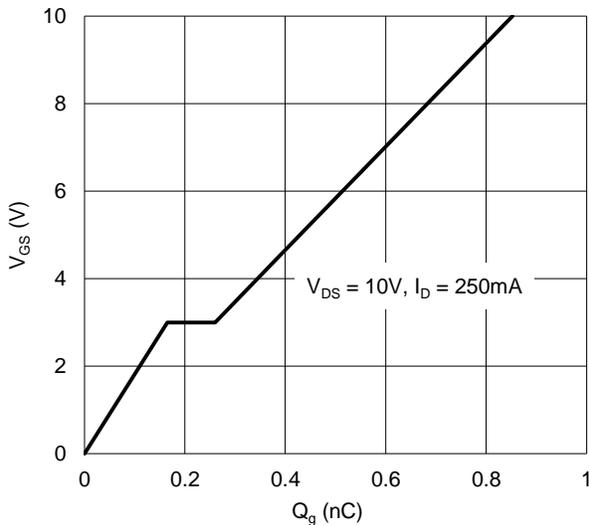


Figure 11. Gate Charge

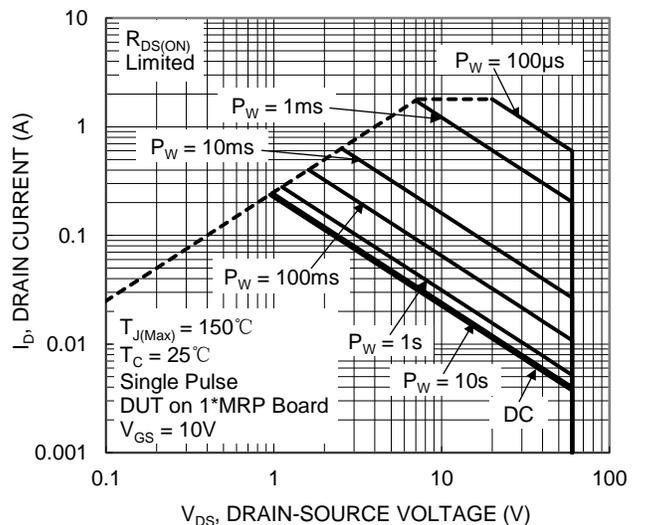


Figure 12. SOA, Safe Operation Area

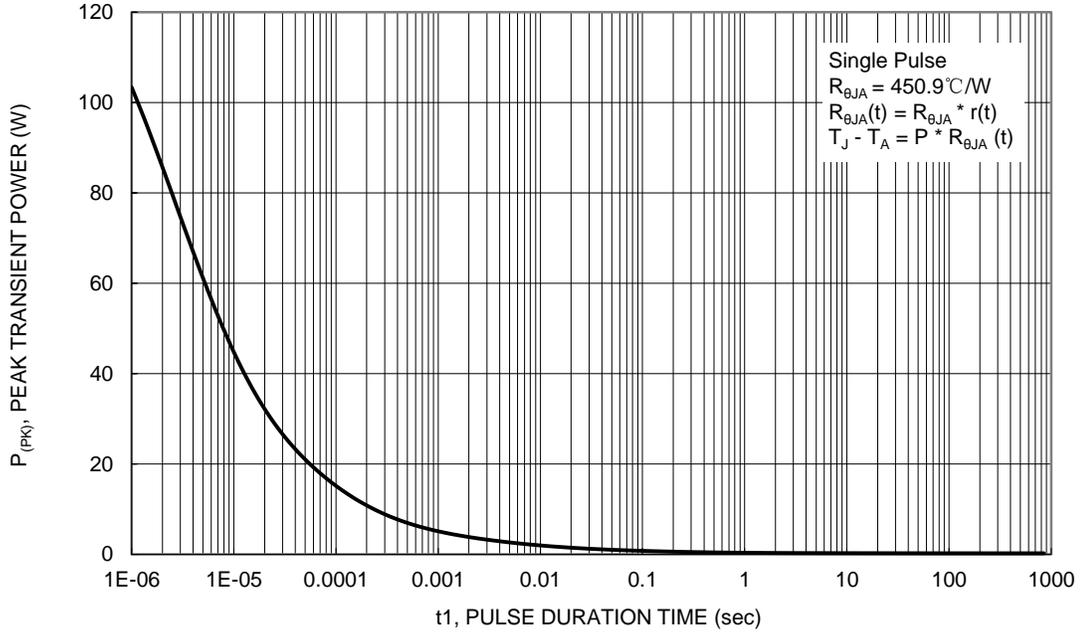


Figure 13. Single Pulse Maximum Power Dissipation

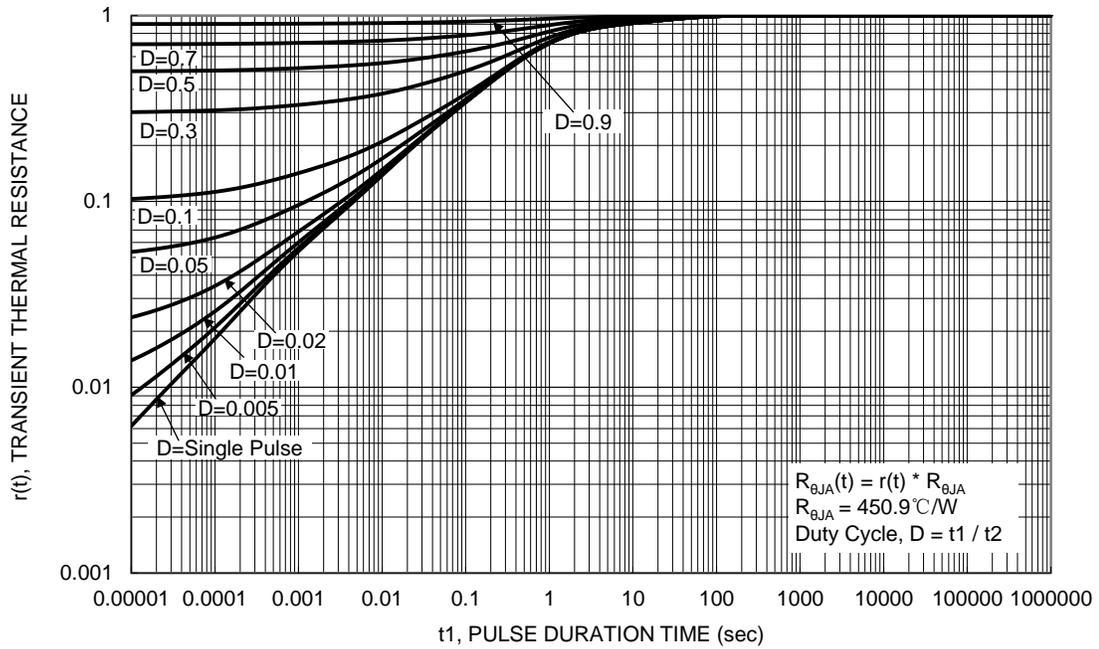
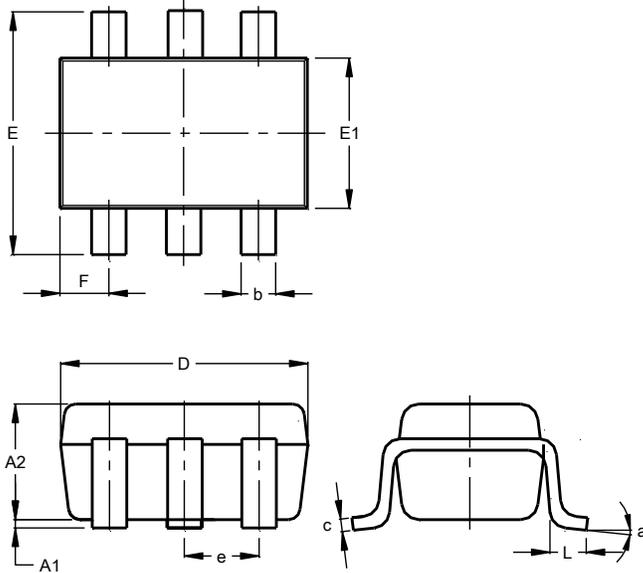


Figure 14. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363

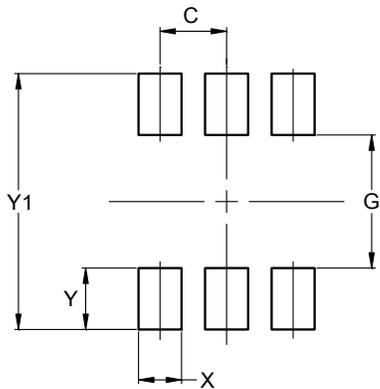


SOT363			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	0.95
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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